

PATENT NUMBER

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APPLICATION NO. 09/917731	CONT/PRIOR	CLASS 438	SUBCLASS 301	ART UNIT 2812	EXAMINER Roman
APPLICANTS	Mohamed Inam Joe Fulton Zia Hossain Masami Tanaka				
TITLE	Method for manufacturing a high voltage MOSFET semiconductor device with enhanced charge controllability				

PTO-2040
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ISSUING CLASSIFICATION								
ORIGINAL			CROSS REFERENCE(S)					
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)					
INTERNATIONAL CLASSIFICATION								

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drawg.	Figs. Drawg.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed. <input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S. Patent, No. _____ _____	(Assistant Examiner) (Date)		NOTICE OF ALLOWANCE MAILED	
			ISSUE FEE	
	(Primary Examiner) (Date)		Amount Due	Date Paid
<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.	(Local Instruments Examiner) (Date)		ISSUE BATCH NUMBER:	

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